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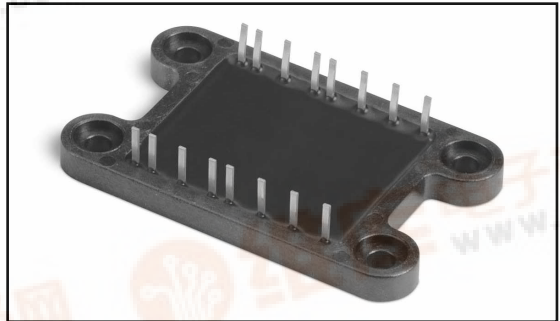
MODEL 7721 SERIES

H Bridge

Power Module

Drives DC motors, transformers and other loads. Paralleled ultrafast diodes included. Standard applications are off-line DC motor control and power conversion.

NEW PRODUCT



MODELS/RANGE

7721-1A	22A 500V IGBTs with 8A 600V ultrafast diodes
7721-2A	32A 600V IGBTs with 25A 600V hyperfast diodes

FEATURES AND BENEFITS

- Saves significant space and assembly time
- Modern design reduces heatsink cost
- Low cost
- Thin package (.200) easily fits between PCB and heatsink
- Internal temperature sensing for fastest possible response
- Replaces 8 each TO-220 or TO-247 discrete power semiconductors
- Custom designs accept any IGBTs or FETs up to size 5 with parallel diodes
- Custom module versions available for specific applications

Example: 3 phase motor drives & rectifier bridges, power servo amplifiers, solenoid drivers, solid state relays, audio amplifiers, and high-power DC/DC converters.

Specifications subject to change without notice.

ELECTRICAL CHARACTERISTICS (7721-1A)

Parameter	Symbol	Conditions ¹	Min.	Typ.	Max.	Units
Q1-Q4 IGBT						
Continuous Collector Current	I_C	$T_C = 25^\circ\text{C}$			40	A
		$T_C = 100^\circ\text{C}$			22	A
Pulsed Collector Current	I_{CM}				80	A
Reverse Avalanche Energy	E_{AVR}				15	mJ
Collector Leakage Current	I_{CES}	$V_{GE} = 0V, V_{CE} = 500V$			250	μA
Saturation Voltage	$V_{CE(ON)}$	$I_C = 22A, V_{GE} = 15V$		2.4	3.0	V
		$I_C = 40A, V_{GE} = 15V$		2.8		V
Gate Threshold Voltage	$V_{GE(TH)}$	$V_{CE} = V_{GE}, I_C = 250\mu\text{A}$	3.0		5.5	V
Gate Leakage Current	I_{GES}	$V_{GE} = \pm 20V$			± 100	nA
Total Gate Charge (turn on)	Q_g	$I_C = 22A, V_{CC} = 400V, V_{GE} = 15V$		55	83	nC
Gate Emitter Charge (turn on)	Q_{ge}	$I_C = 22A, V_{CC} = 400V, V_{GE} = 15V$		11	17	nC
Gate Collector Charge (turn on)	Q_{gc}	$I_C = 22A, V_{CC} = 400V, V_{GE} = 15V$		19	29	nC
Turn Off Delay Time	$t_{d(off)}$	$I_C = 22A, V_{CC} = 400V, V_{GE} = 15V, R_G = 10\Omega \text{ w/tail}$		100	150	ns
Fall Time	t_f	$I_C = 22A, V_{CC} = 400V, V_{GE} = 15V, R_G = 10\Omega \text{ w/tail}$		56	100	ns
Total Switching Loss	E_{ts}	$I_C = 22A, V_{CC} = 400V, V_{GE} = 15V, R_G = 10\Omega \text{ w/tail}$		.55	.70	mJ
Input Capacitance	C_{ies}	$V_{GE} = 0V, V_{CC} = 30V, f = 1\text{MHz}$		1400		pF
Output Capacitance	C_{oes}	$V_{GE} = 0V, V_{CC} = 30V, f = 1\text{MHz}$		250		pF
Reverse Transfer Capacitance	C_{res}	$V_{GE} = 0V, V_{CC} = 30V, f = 1\text{MHz}$		42		pF
Junction Temperature	T_J				150	$^\circ\text{C}$
Thermal Resistance	R_{thjc}				.94	$^\circ\text{C/W}$
D1-D4 Fred Diodes						
Reverse Leakage Current	I_R	$V_R = 600V$			20	μA
		$V_R = .8 \times 600V, T_J = 125^\circ\text{C}$			1.5	mA
Forward Voltage	V_F	$I_F = 8A$			1.5	V
		$I_F = 8A, T_J = 150^\circ\text{C}$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F = 1A, -di/dt = 50A/\mu\text{s}, V_R = 30V$		35	50	ns
Junction Temperature	T_J				150	$^\circ\text{C}$
Thermal Resistance	R_{thjc}				3.1	$^\circ\text{C/W}$
TH1 NTC Thermistor						
Resistance	R_{25}	$I = 1\text{mA}$	22.5	25	27.5	K Ω
Resistance Ratio	R_T/R_{25}	$t = 80^\circ\text{C}$		.126		
		$t = 90^\circ\text{C}$		.0916		
		$t = 100^\circ\text{C}$		.0679		
		$t = 110^\circ\text{C}$		.0511		
Dissipation Constant	P_D			1.0		mW/ $^\circ\text{C}$
Thermal Time Constant	t				10	sec

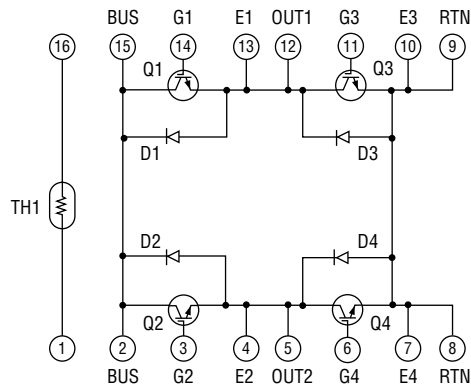
1 - TCase = 25°C unless otherwise specified.

ELECTRICAL CHARACTERISTICS (7721-2A)

Parameter	Symbol	Conditions ¹	Min.	Typ.	Max.	Units
Q1-Q4 IGBT						
Continuous Collector Current	I_C	$T_C = 25^\circ\text{C}$			60	A
		$T_C = 90^\circ\text{C}$			32	A
Pulsed Collector Current	I_{CM}				120	A
Collector Leakage Current	I_{CES}	$V_{GE} = 0V, = .8 \times 600V$			200	μA
		$V_{GE} = 0V, V_{CE} = .8 \times 600V, T_J = 125^\circ\text{C}$			1	mA
Saturation Voltage	$V_{CE(ON)}$	$I_C = 32A, V_{GE} = 15V$			2.5	V
Gate Threshold Voltage	$V_{GE(TH)}$	$V_{CE} = V_{GE}, I_C = 250\mu\text{A}$	2.5		5.0	V
Gate Leakage Current	I_{GES}	$V_{GE} = \pm 20V$			± 100	nA
Total Gate Charge (turn on)	Q_g	$I_C = 32A, V_{CC} = 300V, V_{GE} = 15V$		125	150	nC
Gate Emitter Charge (turn on)	Q_{ge}	$I_C = 32A, V_{CC} = 300V, V_{GE} = 15V$		23	35	nC
Gate Collector Charge (turn on)	Q_{gc}	$I_C = 32A, V_{CC} = 300V, V_{GE} = 15V$		50	75	nC
Turn Off Delay Time	$t_{d(off)}$	$I_C = 32A, V_{CC} = 400V, V_{GE} = 15V, R_G = 4.7\Omega$		100	200	ns
Fall Time	t_f	$I_C = 32A, V_{CC} = 400V, V_{GE} = 15V, R_G = 4.7\Omega$		80	150	ns
Total Switching Loss	E_{ts}	$I_C = 32A, V_{CC} = 400V, V_{GE} = 15V, R_G = 4.7\Omega$		.8	1.6	mJ
Input Capacitance	C_{ies}	$V_{GE} = 0V, V_{CC} = 25V, f = 1\text{MHz}$		2500		pF
Output Capacitance	C_{oes}	$V_{GE} = 0V, V_{CC} = 25V, f = 1\text{MHz}$		230		pF
Reverse Transfer Capacitance	C_{res}	$V_{GE} = 0V, V_{CC} = 25V, f = 1\text{MHz}$		70		pF
Junction Temperature	T_J				150	$^\circ\text{C}$
Thermal Resistance	R_{thjc}				.60	$^\circ\text{C/W}$
D1-D4 Fred Diodes						
Reverse Leakage Current	I_R	$V_R = 600V$		1	500	μA
		$V_R = .600V, T_J = 150^\circ\text{C}$		.3	1.5	mA
Forward Voltage	V_F	$I_F = 25A$		1.5	2.8	V
		$I_F = 25A, T_J = 150^\circ\text{C}$		1.3	2.5	V
Reverse Recovery Time	t_{rr}	$I_F = 1A, -di/dt = 100A/\mu\text{s}$		30	40	ns
Junction Temperature	T_j				175	$^\circ\text{C}$
Thermal Resistance	R_{thjc}				1.2	$^\circ\text{C/W}$
TH1 NTC Thermistor						
Resistance	R_{25}	$I = 1\text{mA}$	22.5	25	27.5	K Ω
Resistance Ratio	R_T/R_{25}	$t = 80^\circ\text{C}$		.126		
		$t = 90^\circ\text{C}$		.0916		
		$t = 100^\circ\text{C}$		.0679		
		$t = 110^\circ\text{C}$		.0511		
Dissipation Constant	P_D			1.0		mW/ $^\circ\text{C}$
Thermal Time Constant	t				10	sec

1 - TCase = 25°C unless otherwise specified.

SCHEMATIC



ORDERING INFORMATION

Model 77 2 1 -1A

Package Size _____

Power Level:
 -1A = 500V, 22A, IGBT
 -2A = 600V, 32A, IGBT

Circuit Function:
 1 = H Bridge

OUTLINE DIMENSIONS (Inch)

